

Theoretical investigation of room-temperature spin-filtering in lattice-matched fcc GaAs/CrAs/GaAs heterostructures

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Based on the assumption that thin layers of fcc CrAs can be sandwiched lattice-matched in between GaAs we perform a theoretical study of spin filtering in $[1,0,0]$ GaAs/CrAs/GaAs heterostructures. The electronic structure of fcc GaAs, CrAs, and GaAs/CrAs heterostructures is obtained within LMTO local spin-density functional theory. Relevant segments of the computed band structure are mapped onto an effective nearest-neighbor $sp^3d^5s^*$ tight-binding model from which, together with the computed band offset, the effective Hamiltonian of the heterostructure is constructed. The current-voltage characteristics are computed within a non-equilibrium Green's function formalism and for several temperatures and thicknesses of the CrAs layer. The results from this investigation indicate that high spin polarization should be feasible with ideal GaAs-CrAs-GaAs heterostructures and persist even at room temperature.

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I. INTRODUCTION

The identification and design of high-efficiency all-semiconductor spin filtering devices which operate at room temperature and at zero external magnetic field are of profound interest for spintronic applications.^{1,2} In spite of some success, for example regarding improved spin injection from ferromagnets into Si, progress has been moderate. Dilute magnetic semiconductors, such as GaMnAs, which have been grown most successfully with good quality of interfaces onto nonmagnetic fcc semiconductors, generally, have critical temperatures far below room temperature.^{3,4} Growing high-quality GaMnAs layers within heterostructures proves to be more difficult than in the bulk. Most likely, due to structural problems in the form of unwanted defects leading to free-carrier compensation, an inevitable disorder in ternary alloys, and limitations to the hole doping levels in the semiconductor contact layers, in experiment, ferromagnetic order appears to be difficult to establish and to maintain under bias in AlGaAs/GaMnAs heterostructures.^{5,6} Signatures of (weak) quantum confinement effects associated with GaMnAs quantum wells in GaAlAs/GaMnAs single- and double barrier heterostructures have been reported in the literature.⁵ Using one $\text{Ga}_{0.96}\text{Mn}_{0.04}\text{As}$ contact layer on an asymmetric GaAlAs/GaMnAs heterostructure magnetization-dependent negative-differential-resistance has been observed.⁷ A similar TMR experiment has been performed recently, in which resonant tunneling in non-magnetic AlGaAs/GaAs/AlGaAs was used to control the hole current.⁸

MA or MSb compounds, with M denoting a transition metal, such as V, Cr, Mn in the bulk are not

stable in the fcc phase. Even in thin layers on an fcc substrate, such as GaAs, they appear to be difficult to grow in this phase.⁹⁻¹² Some noteworthy exceptions are the reports of the experimental realization of fcc MnAs quantum dots on GaAs and the growth of thin layers of CrAs on GaAs substrates.^{13,14} Recent experiments have suggested that CrAs is a halfmetallic ferromagnet which, when grown epitaxially in the fcc structure on top of GaAs, displays ferromagnetic behavior well above room temperature.¹⁴⁻¹⁶ Ab-initio studies of the system have led to the prediction that the Curie temperature of fcc CrAs may be as high as 1000 K.^{12,17-19} The electronic structure of GaAs / CrAs heterostructures has been studied by Bengone *et al.*²⁰ They also studied transport properties through GaAs/CrAs/GaAs trilayers. It has to be noted at this point that density functional theory (DFT) based calculations, as well as some experimental results^{11,21}, indicate that the fcc-structure of thin film CrAs is energetically unstable. It has therefore been argued that the experimentally observed ferromagnetic behavior may be caused by magnetic defects near the heterointerface and that no half-metallicity may be present in thin layers of CrAs grown on GaAs substrates at all.

In the recent past we have investigated the effect of electronic correlations upon the half-metallicity of stacked short period $(\text{CrAs})_\ell/(\text{GaAs})_\ell$ ($\ell \leq 3$) superlattices along $[001]$. Our results indicate that the minority spin half-metallic gap is suppressed by local correlations at finite temperatures and continuously shrinks on increasing the heterostructure period. As a consequence, at the Fermi level, the polarization is significantly reduced, while dynamic correlations produce only a small deviation in magnetization²². Essentially the same effect was found for defect-free digital magnetic heterostructures δ -doped with Cr and Mn²³. In addition

both studies indicate that the minority spin highest valence states below the Fermi level are localized more in the GaAs layers while the lowest conduction band states have a many-body origin derived from CrAs. Therefore independent of the presence of electronic correlations in these heterostructures holes and electrons may remain separated among different layers which may be detected in photo-absorption measurements. From these combined density functional and many-body calculations^{22,23}, briefly described above, it is not possible to establish whether the many-body-induced states within the minority spin channel are conducting or not. It is of great interest to study transport through such heterostructures.

The aim of the present paper is to explore spin filtering in GaAs/ single-layer-CrAs/GaAs heterostructures under the assumption of perfect fcc lattice matching. As will be shown below half-metallicity is not a necessary ingredient for efficient spin filtering. Essential are the interfacial properties and the spin-selective band matching (bias-dependent “band alignment”) between the CrAs and GaAs layers. Within the current work we determine the band matching by aligning the bands according to the band offset obtained within the local spin-density approximation (LSDA) results. The interfacial properties are modeled ad hoc by keeping constant the As onsite energies appearing in our tight-binding model throughout the device. We demonstrate in the current work that ideal GaAs /CrAs/GaAs heterostructures should function as room temperature spin filters regardless of half-metallicity.

Our theoretical approach consists of three main parts: In a first step we determine the spin-dependent band structure of lattice matched fcc bulk CrAs and a $[1,0,0]$ (GaAs)₆ / (CrAs)₆ supercell using the LMTO method. This method is also used to calculate the electronic structure of GaAs. From these calculations we determine the band offset between the two materials, as well as the spin-dependent bulk electronic structure of CrAs. We then map the electronic structure of the bulk materials onto an effective 20-orbital $sp^3d^5s^*$ nearest neighbor tight-binding (TB) model. In the final step we calculate the current-voltage (I-V) characteristics within the non-equilibrium Green’s function formalism.

This article is structured as follows. In Sec. II we present the theoretical approach and the results for the electronic structure. In Sec. III we describe the mapping procedure onto the tight-binding model. The transport model and results for several layer thicknesses and temperatures are discussed in Sec. IV. Summary and conclusions are given in Sec. V.

II. LMTO ELECTRONIC STRUCTURE CALCULATIONS AND THE CRAS/GAAS $[1,0,0]$ BAND OFFSET

The electronic structures of bulk zinc-blend (ZB) GaAs, bulk ZB CrAs as well as of a (GaAs)₆(CrAs)₆ supercell have been determined employing the LMTO-ASA code as developed by Jepsen and Andersen.^{24,25} This code has been employed previously to explore the electronic structure of bulk ZB CrAs and thin-layer fcc GaAs/CrAs superlattices. In particular the half-metallic behavior as a function of superlattice period and lattice constants was investigated.^{22,26} Details of this approach can be found in the literature.²⁵

The electronic structure model is based on LSDA omitting spin-orbit interaction and corrections for strong correlations as provided, for example, by the dynamic-mean-field-theory (DMFT)²⁷ or variational cluster approach (VCA)^{28,29}. The omission of these corrections clearly leaves open the question as to the accuracy of the results for fcc CrAs. However, it has been shown by Chioncel et al.^{22,26} that the inclusion of correlations does not affect the magnetization. LSDA or its gradient-corrected approximation (GGA) produce band gaps that are typically at least 30% smaller than the experimental values for almost all semiconductors and insulators. In the case of half-metals one may speculate that this problem is not serious, as the dielectric response of half-metals is of metallic type. State-of-the art *GW* calculations show the tendency to improve on the gap problem for semiconductors, however, applied to half-metallic La_{0.7}Sr_{0.3}MnO₃ they over-estimate the half-metallic gap.³⁰ The well-known GaAs band gap of 1.52 eV at low temperature is strongly underestimated by the present spin-DFT method, predicting a value of about 0.35 eV, while the overall features in the vicinity of the band gap are reproduced reasonably well. Since we do not study transport across the main energy gap, such as in Zener tunneling, in what follows we consider two distinct cases: (i) we leave the electronic structure unchanged, i.e. we use the GaAs band structure with the underestimated band gap, and (ii) we scissor the GaAs electronic structure to the experimentally observed value of 1.52 eV. For want of better knowledge, the electronic structure of majority and minority spin fcc CrAs was not scissored. Previous results showed that the detailed nature of states around E_F in bulk CrAs is changed when different lattice constants or models for electronic correlations are considered.²³ Furthermore, we consider n-doped GaAs such that the spin-orbit effects, at least in GaAs, can be neglected. Here clearly the final answer as to the accuracy of the electronic structure model can only be given by comparison to experiment. With the present work, in fact, we hope to kindle interest in further experimental studies of this material combination.

Since the GaAs band structure is well known and, except for the band gap, is fairly well reproduced within the LMTO-ASA code, here we mainly discuss the results

obtained for bulk fcc CrAs with the GaAs lattice constant $a_l = 5.65$ Å. The electronic structure for majority and minority carriers is shown, respectively, in Figs. 1 and 2 (red solid lines). For the minority carriers a gap of about 1.8 eV is predicted. A more detailed analysis of the electronic structure shows the origin of the valence band edge in the As-p - Cr-d hybrid orbitals while conduction band edge states are dominated by the Cr-d orbitals, see Chioncel et al.^{22,26}.

Let us emphasize an interesting point: We observe from the ab-initio calculations that the lattice constant chosen for bulk fcc CrAs determines whether CrAs is half-metallic or not, see also^{22,26}. Since the bulk band structures of GaAs and CrAs are shifted relative to each other by the band offset, as discussed below, we obtain that half-metallicity of the CrAs layer is not compulsory for the realization of a spin filter. A necessary ingredient is a high degree of spin-dependence in the CrAs band structure.

In the spirit of core level spectroscopy, the band alignment (band-offset) at the [1,0,0] GaAs/CrAs interface was determined using the average energy of the low-lying As-s bands of the two bulk materials for a reference state. We computed the center of energy of these bands for bulk fcc CrAs Δ_C , bulk fcc GaAs Δ_G (relative to the valence band edge), as well as for the As atoms embedded in the Ga and Cr environment in a $(\text{GaAs})_6(\text{CrAs})_6$ supercell Δ_{GG} and Δ_{CC} (relative to the Fermi energy). The center of energy of one particular band is obtained by calculating the fat-band weights with the help of the ab-initio LMTO-ASA code and using them as a weight when performing the average over the first Brillouin zone. The band offset Δ is calculated according to³¹

$$\Delta = \Delta_G - \Delta_C + \Delta_{GG} - \Delta_{CC}. \quad (1)$$

With this procedure we obtain $\Delta_1 = 0.60$ eV and $\Delta_2 = 0.55$ eV, respectively, for majority and minority spin. Here it should be recalled that the determination of the band-offset is based on a $(\text{GaAs})_6(\text{CrAs})_6$ supercell. A reasonable error estimate is difficult, since it involves not only the procedure of finding the center of energy for the As-s band but also the underlying electronic structure model. In the present calculations we have used the LSDA-ASA (atomic sphere approximation) method and the potentials were converged to better than 10^{-6} Ry, with the same accuracy for the center of the bands and related quantities.

In Figs. 1 and 2 we show, on top of the electronic structure of majority- and minority-spin CrAs, the electronic structure of GaAs for case (i) (un-scissored gap) and case (ii) (scissored gap) taking into account the computed band offset. It can now clearly be seen that carriers injected from n-GaAs near the Γ -point do not reach the main energy gap region of bulk CrAs. Even in case of p-doping of the GaAs contact layers, this region can only be reached under an applied bias exceeding approximately 0.3 V, as can be observed from an inspection of Fig. 2.

Moreover, scissoring of the GaAs band gap does not

significantly change the spectral overlap of the lowest GaAs conduction band with the CrAs bands near the Γ point. The situation is rather different for minority carriers, however, here the overlap of the lowest GaAs conduction band in both cases occurs with fairly flat CrAs bands of low mobility.

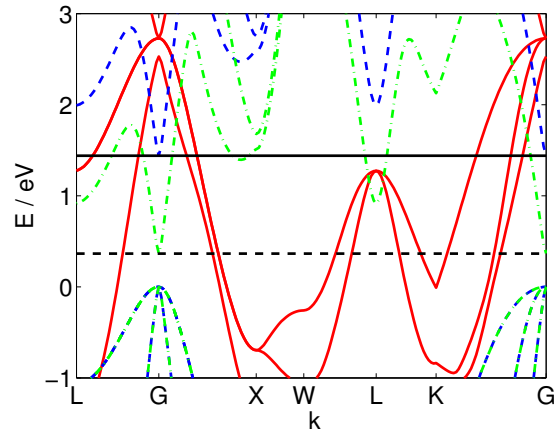


Figure 1: (Color online) Majority spin CrAs ab-initio band structure (red solid line), scissored, and un-scissored GaAs band structure (blue dashed line and green dash-dotted line). The Fermi energy $E_F = 0.01$ eV above the conduction band minimum of GaAs is indicated by the horizontal lines (solid: scissored GaAs, dashed: un-scissored GaAs).

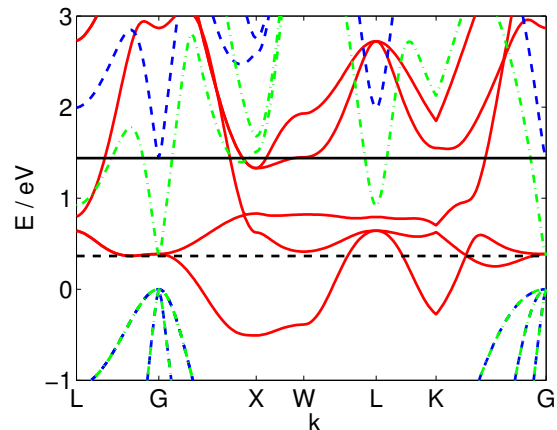


Figure 2: (Color online) Minority spin CrAs ab-initio band structure (red solid line) and scissored as well as un-scissored GaAs band structure (blue dashed line and green dash-dotted line). The Fermi energy $E_F = 0.01$ eV above the conduction band minimum of GaAs is indicated by the horizontal lines (solid: scissored GaAs, dashed: un-scissored GaAs).

III. EFFECTIVE $\text{sp}^3\text{d}^5\text{s}^*$ TIGHT-BINDING MODEL

In the second step the ab-initio electronic structure ε_n^{LSDA} of GaAs as well as of majority- and minority-spin CrAs individually is mapped onto an effective $\text{sp}^3\text{d}^5\text{s}^*$ nearest neighbor TB model.³²⁻³⁴

In principle, this step can be avoided if the LSDA wave functions were used to express the transmission function of the heterostructure, as for example proposed within the SIESTA DFT approach.³⁵ The trade-off of an approach which is based on the L(S)DA one-particle wave functions, however, is that its validity ad hoc is questionable, since the wave functions used in the Kohn-Sham variational principle do not allow a direct physical interpretation so that their connection to the S-matrix is not obvious. The use of ground state wave-functions would definitely limit one to the linear-response regime, since the transmission function would be obtained for zero external bias only. In general LDA bulk band-structure calculations are flawed regards to producing the correct energy gap. While for bulk GaAs it is known which scissoring procedure is required to fix this problem, for fcc CrAs it is not. For an ab-initio supercell calculation for GaAs/CrAs heterostructures a simple "scissor operation" does not work at all. These difficulties have convinced us to follow a mapping ("downfolding") approach from the ab-initio band structure calculation to an empirical tight-binding model.

The benefits from downfolding onto an tight-binding model are that, for the energy window of interest, an effective single-particle Hamiltonian for the individual bulk systems, as well as the bulk heterostructure in their respective ground state is constructed. For each bulk system an individual scissor operation can be employed if deemed necessary. Subsequently, the Hamiltonian of a given heterostructure can be put together layer by layer. Note that the calculation procedure for the band alignment (here between GaAs and CrAs) is independent of scissoring. Moreover, an applied electric bias and bias-dependent mean-field corrections can be added in self-consistent fashion, as utilized by some of us recently for similar systems.^{36,37} This convenient layer-by-layer construction can be employed in the construction of the non-equilibrium Green's function components also and has been used in the calculations below. A further advantage of the approach chosen within this work is that we know the k -dependence of the bulk TB Hamiltonians analytically via the structure factors. Hence, the influence of small deviations in the TB binding parameters can be investigated in a systematic manner. On the other hand, the tight-binding parameters cannot be determined uniquely and must be understood as fitting parameters only. Moreover, there is no clear prescription of how to interpolate them at a heterointerface. A detailed study of the benefits and caveats of such an approach will be given in the near future.³⁸

The formal process of downfolding is executed using a

genetic algorithm as implemented in Matlab and minimizing the cost functional

$$K(\xi) = \sqrt{\sum_{nk} a_n(k) [\varepsilon_n^{LSDA}(k) - \varepsilon_n^{TB}(k, \xi)]^2}. \quad (2)$$

Here, $a_n(k)$ are normalized weights where n is the band index and k the wave vector, ξ denotes the set of 31 independent TB parameters and $\varepsilon_n^{TB}(k, \xi)$ is the TB band structure as a function of k and ξ . The weights $a_n(k)$ are used to restrict and/or focus the fit to the part of the band structure which contributes to charge transport. This ensures that the energy bands are well represented by the TB fit and no "spurious bands" appear inside this energy window.

The fit procedure is executed in two steps: In a first step we fit the majority and minority spin band structure of CrAs independently without any further restrictions. In a second step we fit the GaAs band structure under the constraint that all As onsite energies have to have the same value as in CrAs. Let us briefly discuss the implications of such a fitting procedure: First of all, we obtain two different sets of TB parameters for GaAs since we fit the two CrAs band structures independently and then restrict the GaAs parameters depending on spin orientation. Had we included the spin-orbit interaction into our model, two distinct sets of TB parameters for GaAs would come more natural, however, in any case the values obtained must be considered best fits under given constraints. Such a constraint on the GaAs TB parameters is motivated as follows: the As onsite energies have to be equal in both materials in order to avoid the question of how to choose the onsite energies of As near the GaAs/CrAs interface, in particular, the interface As sandwiched between a Cr and a Ga cation. Since such a fitting procedure in general will not yield unique TB parameters, this constraint also helps to limit the number of possible parameter sets.

All in all we perform the downfolding process for four different combinations: (A) majority-spin CrAs and scissored GaAs, (B) majority-spin CrAs and un-scissored GaAs, (C) minority-spin CrAs and scissored GaAs, and (D) minority-spin CrAs and un-scissored GaAs. The TB parameters which were identified as optimal for each of the four cases are listed in the Appendix. The fits for GaAs together with the ab-initio band structure and the fits of majority- and minority-spin CrAs are given in Figs. 3, 4, 5 and 6. In view of the fact that the computed ab-initio electronic structure can at best capture the overall features of the actual electronic band structure the obtained TB fits are highly satisfactory.

In principle, the spin-orbit interaction can be included in the TB model following the work of Chadi.³⁹ However, since the LMTO-ASA code itself currently does not feature spin-orbit interactions, its implementation at the TB level would require the introduction of further (and somewhat arbitrary) parameters into our model, in particular for CrAs. Furthermore, we shall focus on transport with n-doped GaAs buffer layers so that a detailed

account of the spin-orbit interaction in the GaAs electronic structure will not really be important here.

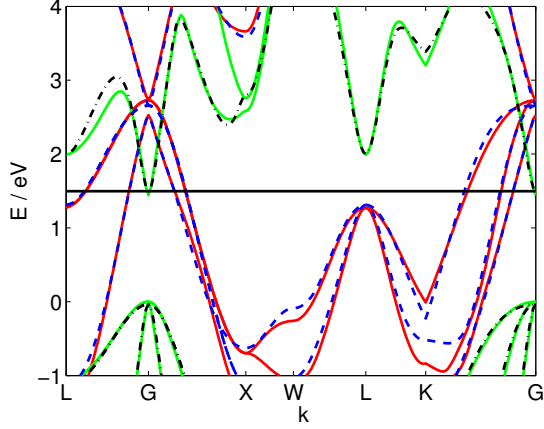


Figure 3: (Color online) Scenario (A): majority spin CrAs ab-initio band structure (red solid line), CrAs TB-fit (blue dashed line), scissored GaAs band structure (green solid line) and GaAs TB fit (black dashed line). The Fermi energy $E_F = 0.01$ eV above the conduction band minimum of GaAs is indicated by the horizontal solid line.

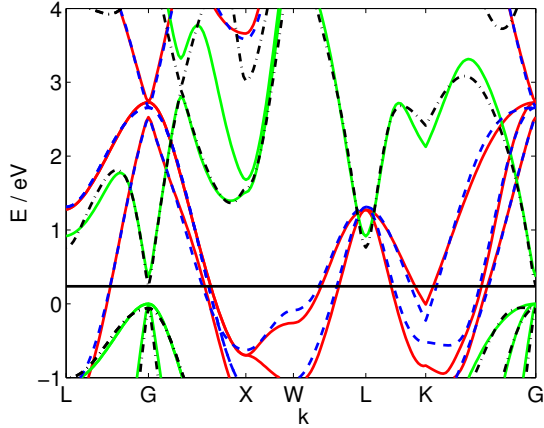


Figure 4: (Color online) Scenario (B): majority spin CrAs ab-initio band structure (red solid line), CrAs TB-fit (blue dashed line), un-scissored GaAs band structure (green solid line) and GaAs TB fit (black dashed line). The Fermi energy $E_F = 0.01$ eV above the conduction band minimum of GaAs is indicated by the horizontal solid line.

IV. STEADY-STATE TRANSPORT

The I-V-characteristics of the heterostructure is calculated within a non-equilibrium Green's function approach which has been adapted from our recent study of GaMnAs-based heterostructures, to which we refer for further details and references.^{36,37,40,41}

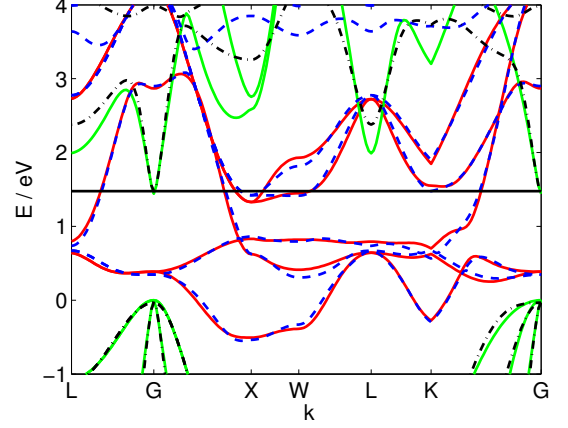


Figure 5: (Color online) Scenario (C): minority spin CrAs ab-initio band structure (red solid line), CrAs TB-fit (blue dashed line), scissored GaAs band structure (green solid line) and GaAs TB fit (black dashed line). The Fermi energy $E_F = 0.01$ eV above the conduction band minimum of GaAs is indicated by the horizontal solid line.

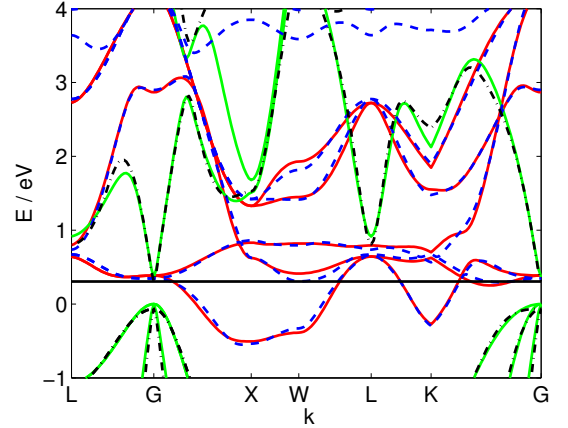


Figure 6: (Color online) Scenario (D): minority spin CrAs ab-initio band structure (red solid line), CrAs TB-fit (blue dashed line), un-scissored GaAs band structure (green solid line) and GaAs TB fit (black dashed line). The Fermi energy $E_F = 0.01$ eV above the conduction band minimum of GaAs is indicated by the horizontal solid line.

The Hamiltonian of the GaAs/CrAs/GaAs heterostructure is obtained by performing a partial Wannier transformation from the wave vector k to $(x, k_{\parallel})$, where x denotes the $[1,0,0]$ growth direction of the crystal and $k_{\parallel}$ is the in-plane (parallel) k-vector⁴¹,

$$|nbjk_{\parallel}\rangle = \frac{1}{\sqrt{L_{BZ}}} \int dk_x \exp\left(-ik_x j \frac{a_L}{4}\right) |nbk\rangle, \quad (3)$$

where $L_{BZ} = \frac{8\pi}{a_L}$ and j labels the layer.

The resulting one-particle Hamiltonian is of the single-

particle form

$$H(k_{\parallel}) = \sum_{i,\sigma\sigma'} \varepsilon_{\sigma,\sigma'}^{(i)}(k_{\parallel}) c_{i,\sigma}^{\dagger}(k_{\parallel}) c_{i,\sigma'}(k_{\parallel}) + \sum_{i,\sigma\sigma'} t_{\sigma\sigma'}^{(i)}(k_{\parallel}) c_{i+1,\sigma}^{\dagger}(k_{\parallel}) c_{i,\sigma'}(k_{\parallel}) + \text{h.c.}, \quad (4)$$

with $c_{i,\sigma}^{\dagger}(k_{\parallel})$ ($c_{i,\sigma}(k_{\parallel})$) denoting the creation (annihilation) operator for site i and orbital σ . $\varepsilon_{\sigma\sigma'}^{(i)}(k_{\parallel})$ and $t_{\sigma\sigma'}^{(i)}(k_{\parallel})$ are onsite and hopping matrix elements. The semi-infinite GaAs leads are taken into account by evaluating the associated self-energies and feeding them into the system's Dyson equation.⁴² The surface Green's functions are obtained with the help of an algorithm suggested by Sancho et al.⁴³ The transmission function $T(E, k_{\parallel})$ for total energy E and in-plane momentum $k_{\parallel}$ is calculated via

$$T(E, k_{\parallel}) = \text{Tr} [\Gamma_R G^R \Gamma_L G^A]. \quad (5)$$

Here, $G^{R/A}$ are the system's retarded (R) and advanced (A) Green's functions, $\Gamma_{L/R}$ are the coupling functions to the left (L) and right (R) GaAs leads and $\text{Tr}[\cdot]$ is the trace operation. We then compute the steady-state current $j(V_a)$ assuming local thermal equilibrium among the electrons injected from a particular contact using the standard expression from stationary scattering theory⁴²

$$j(V_a) = \frac{2e}{h} \sum_{k_{\parallel}} \int dE T(E, k_{\parallel}) [f_L(E) - f_R(E)], \quad (6)$$

with e , h and $f_{L/R}$ denoting, respectively, the elementary charge, Planck's constant, and the Fermi-Dirac distribution function for the left and right electric contact. V_a enters Eq. (6) in two places: the transmission function $T(E, k_{\parallel})$ and the difference in the quasi-Fermi levels between left and right contact. In order to cut computational cost, we assume a linear voltage drop from the left to the right lead across the simulated structure. This implies a somewhat artificial relationship between the electric field across the structure and the applied bias.^{44,45} In principle, both an effective single-particle potential, an effective exchange splitting, and a self-consistent treatment of charge injection can be implemented into the present model.³⁷ However, while providing a significant reduction in computation time, omission of self-consistency does not significantly reduce the quality of our results in view of other approximations made. Note that the Fermi-Dirac distributions of the GaAs contacts provide the sole temperature dependence in the current model since a temperature dependence of the electronic structure is not considered here.

In what follows we present results for the I-V characteristics of $\text{GaAs}/(\text{CrAs})_{\ell}/\text{GaAs}$ heterostructures for $\ell = 4, 6, 8, 10$. While thin layers of fcc CrAs may be easier to realize experimentally, thicker layers thereof are more realistically described within our approach. The

free carrier density in the n-doped GaAs regions is about $4.5 \times 10^{17} \text{ cm}^{-3}$ at $T = 300 \text{ K}$ ($7.9 \times 10^{16} \text{ cm}^{-3}$ at $T = 0 \text{ K}$), with the quasi-Fermi level held constant at 10 meV above the conduction band edge. The applied bias was varied between zero and 0.2 V. Results for scissored and un-scissored GaAs, respectively, and $\ell = 10$ are shown in Figs. 7 and 8 (mind the semi-logarithmic plot). The overall features of the I-V characteristics agree for both cases: the majority current density clearly dominates the minority current density and, in most bias regions, by several orders of magnitude. However, this effect is more pronounced for the scissored GaAs model. While the majority current is rather insensitive to scissoring, the minority current density is not (we believe that the small oscillations for the 77 K minority case near 1.5 V in Fig. 7 are of numerical origin). The reason is found when inspecting Figs. 1 and 2. It shows that, for un-scissored GaAs at low applied bias, there is a resonance between the GaAs conduction band minimum (dashed line) and CrAs associated bands near the Γ -point. Near the Γ -point these bands are rather flat and so the group velocity is almost zero. Under moderate bias, however, these bands are moved further into resonance (to regions with higher group velocity) with the conduction band of GaAs at the emitter side and the minority current initially rises steeply.

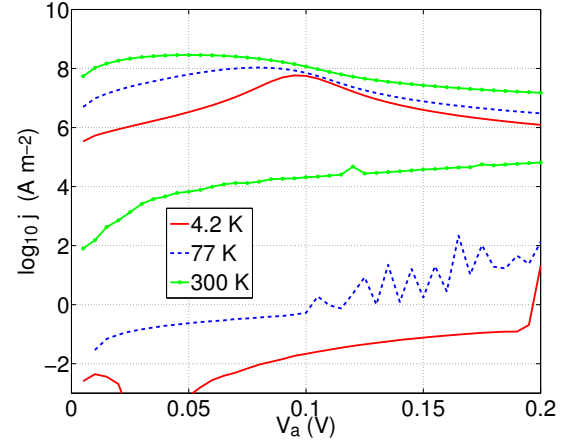


Figure 7: (Color online) Spin-resolved current-voltage characteristics for $\text{GaAs}/(\text{CrAs})_{10}/\text{GaAs}$ and case (A) and (C) (scissored GaAs) for different temperatures ($T = 4.2 \text{ K}$, $T = 77 \text{ K}$, and $T = 300 \text{ K}$). The majority spin current clearly dominates the minority spin current for all voltages and temperatures.

The current spin polarization $P(V_a)$ as a function of applied voltage V_a is defined as

$$P(V_a) = \frac{|j_{\text{maj}}(V_a) - j_{\text{min}}(V_a)|}{|j_{\text{maj}}(V_a) + j_{\text{min}}(V_a)|}. \quad (7)$$

Here, $j_{\text{maj/min}}$ refers to the majority and minority spin current density, respectively. In Figs. 9 and 10, respectively, we display the computed current spin polarization

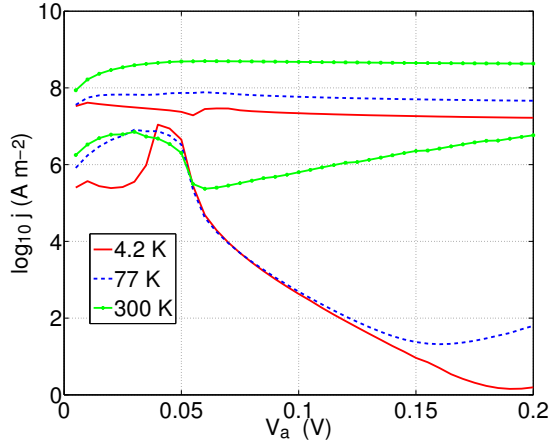


Figure 8: (Color online) Spin-resolved current-voltage characteristics for GaAs/(CrAs)₁₀/GaAs and case (B) and (D) (un-scissored GaAs) for different temperatures ($T = 4.2$ K, $T = 77$ K, and $T = 300$ K). The majority spin current clearly dominates the minority spin current for all voltages and temperatures.

for scissored and un-scissored GaAs and the three different temperatures discussed above.

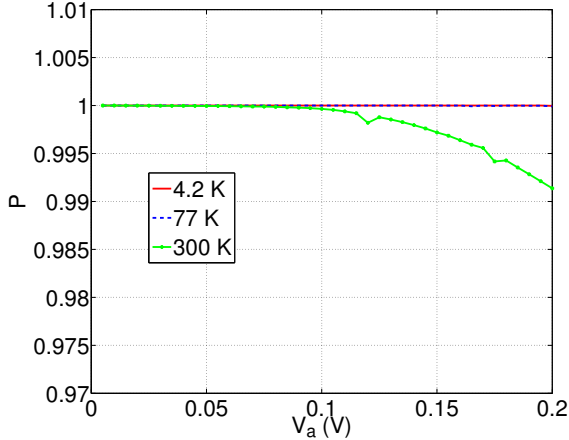


Figure 9: (Color online) Current spin polarization $P(V_a)$ for scissored GaAs for different temperatures ($T = 4.2$ K, $T = 77$ K, and $T = 300$ K).

In Fig. 11 we show the I-V characteristics as obtained for different layers thicknesses, i.e. (GaAs) _{m} /(CrAs) _{ℓ} /(GaAs) _{m} , where $\ell = 4, 6, 8, 10$ and $m = 5$. The results shown in Fig. 11 stem from simulations in which the number of layers of GaAs to the left and the right of CrAs was set to $m = 5$ and kept constant, i.e. the electric field across the CrAs layer at a given voltage increases with decreasing layer thickness. This trend follows the actual physical trend within the device and that of a self-consistent model. Moreover, we note that the actual form of the computed I-V characteristic is only

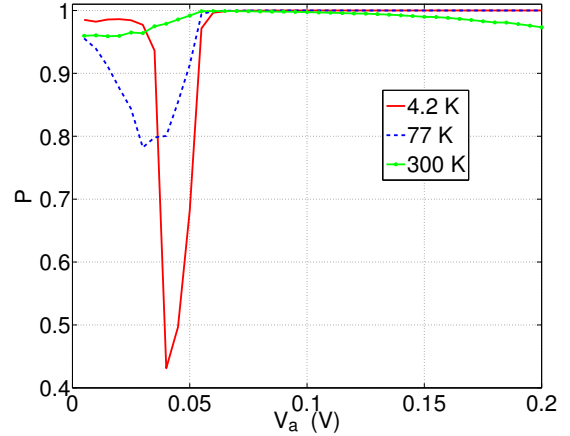


Figure 10: (Color online) Current spin polarization $P(V_a)$ for un-scissored GaAs for different temperatures ($T = 4.2$ K, $T = 77$ K, and $T = 300$ K).

slightly changed if our simulations are performed under equal-electric-field conditions, i.e. $m = 10 - \frac{\ell}{2}$ because the form of the bands involved in the transport of majority carriers (determining their transmission coefficient) is very robust under a slight change of the energy offset, see Figs. 3 and 4.

From Fig. 11 we clearly observe non-Ohmic behavior which is due to the rather complicated electronic structure involved in the transmission probability. We observe, for instance, that the absolute value of the current transmitted through a structure consisting of six layers CrAs is higher for all voltages than when transmitted through four layers. These I-V characteristics indicate that spin-filtering should also be realizable with very thin structures of CrAs, see Fig. 12, which might be easier to fabricate. For $n=4$, the minority current shows nonlinearities which we attribute to resonant transport mediated by states which, in the bulk, give rise to the at bands discussed above. Nevertheless, it has to be kept in mind that the theoretical prediction is less reliable for very thin structures because (i) the modeling of the CrAs layers is based on the Hamiltonian of bulk ZB CrAs and (ii) effects from the interface will become more important for thin layers.

V. DISCUSSION AND CONCLUSIONS

We have performed a model study of transport in GaAs/CrAs heterostructures which is based on the assumption that sufficiently thin layers of fcc CrAs can be grown lattice matched in between a GaAs substrate and capping layer. The bulk electronic structure of fcc GaAs, fcc CrAs, as well as lattice matched single [1,0,0] GaAs/CrAs heterointerfaces were calculated within LSDA and used to determine the band offset between the two materials. For a lattice constant of

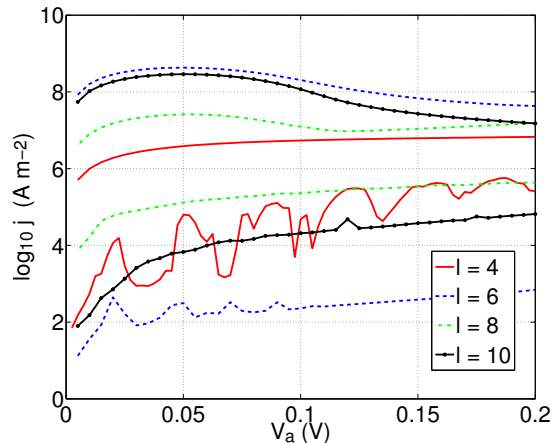


Figure 11: (Color online) I-V characteristics for different layer thicknesses $\ell = 4, 6, 8, 10$.

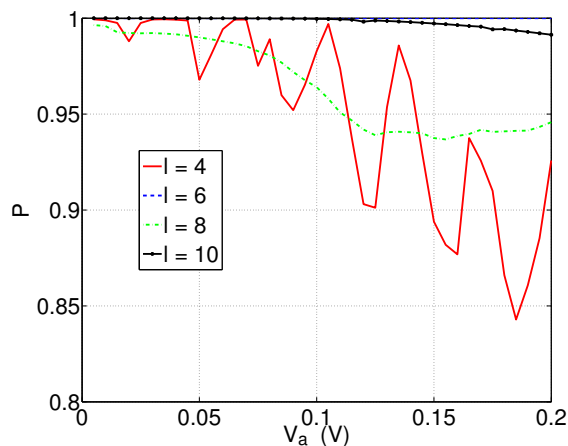


Figure 12: (Color online) Current spin polarization for different layer thicknesses $\ell = 4, 6, 8, 10$.

$a_l = 5.65 \text{ \AA}$ we find that fcc CrAs is a half-metal, with zero gap for one spin orientation (majority carriers) and a gap of 1.8 eV at the X point for the other (minority carriers). The computed band offset of about 0.5 – 0.6 eV, however, aligns the gap region of minority CrAs with the central region of the top valence bands of GaAs. For spin-filtering therefore it is not important

whether the sheet of fcc CrAs lattice-matched to GaAs is half-metallic.

The computed ab-initio spin-dependent electronic structures are downfolded onto TB models which are used to construct the effective Hamiltonian of the of n-GaAs/CrAs/n-GaAs heterostructures consisting of $\ell = 4, 6, 8, 10$ mono-layers of CrAs and to compute the current response within a non-equilibrium Green's function approach. Downfolding was constrained by the requirement that As TB onsite parameters for a given spin orientation be constant throughout the system. We consider carrier injection from n-doped GaAs and our calculations show efficient spin-filtering over a wide parameter range, in particular, regarding the precise band alignment between the GaAs conduction band edge with the CrAs bands, temperature, and layer thickness. Spin-polarization of up to 99 percent is predicted within this model.

A number of potential improvements to the present theoretical approach, such as a more realistic account of correlation, inclusion of the spin-orbit interaction, a self-consistent treatment of transport, etc., can readily be listed and be addressed in future studies. However the main problem currently lies in the fabrication of fcc heterostructures containing layers of transition metal compounds, such as CrAs, MnAs, or VAs, and conventional fcc semiconductors. For MnAs, apart from Mn delta-doped GaAs structures and strained fcc MnAs quantum dots on GaAs, the growth in the fcc apparently has not been achievable. Evidence for fcc CrAs layers on GaAs substrates still seems to be controversial. It is hoped that these promising theoretical results regarding high spin-polarization encourage the materials growth and experimental physics community in the study of semiconductor heterostructures containing transition metal compounds.

VI. ACKNOWLEDGMENTS

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Appendix A: tight-binding parameters

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Table I: tight-binding parameters for bulk CrAs majority and minority spin and the respective GaAs parameters. The anion onsite energies are indicated by the number 1 while the cation is labeled by the number 2. For further notations see³³.

	CrAs maj	GaAs maj (A)	GaAs maj (B)	CrAs min	GaAs min (C)	GaAs min (D)
E_{s1}	2.6574	2.6574	2.6574	4.5703	4.5703	4.5703
E_{s2}	4.3837	4.1719	-11.8119	1.0108	5.5583	-16.4426
E_{p1}	1.2291	1.2291	1.2291	2.0184	2.0184	2.0184
E_{p2}	13.8494	26.2033	11.8069	-6.5536	5.4491	27.2734
E_{d11}	8.2985	8.2985	8.2985	9.9412	9.9412	9.9412
E_{d12}	7.4409	7.4409	7.4409	6.3685	6.3685	6.3685
E_{d21}	-1.3823	15.6055	14.1494	4.5335	4.5941	9.9138
E_{d22}	-1.9278	14.1638	10.6150	0.8616	5.5512	14.2845
E_{s^*1}	18.5203	18.5203	18.5203	-0.6061	-0.6061	-0.6061
E_{s^*2}	1.8607	10.4258	9.3580	9.0261	-2.4055	16.4261
$(ss\sigma)$	-1.1307	15.6358	8.1308	1.3311	0.2533	-0.2897
$(s1p2\sigma)$	0.9972	-2.2562	0.5449	2.9666	0.2245	-1.8973
$(s2p1\sigma)$	-0.1885	7.2869	5.2848	-1.4504	0.7586	7.7539
$(pp\sigma)$	3.2695	-4.9820	3.2030	-3.5148	-2.3875	-0.9973
$(pp\pi)$	-1.9484	2.7602	-2.0813	-0.1283	1.3346	2.9221
$(s1d2\sigma)$	-3.3586	-4.3212	3.9507	0.4038	-0.6059	-1.3790
$(s2d1\sigma)$	3.1659	-3.3578	-1.4149	2.4298	0.6413	-4.6244
$(p1d2\sigma)$	-1.1220	-0.2759	0.1416	0.5525	2.7231	3.8984
$(p1d2\pi)$	0.8269	2.5960	2.5355	0.5372	0.3951	2.0218
$(p2d1\sigma)$	0.1535	2.1035	0.4901	3.7059	-0.2031	0.7540
$(p2d1\pi)$	-1.9975	-3.6283	-2.8348	3.0276	0.9990	1.6321
$(dd\sigma)$	-2.1444	-1.4358	0.7386	-2.1594	0.1633	-0.3069
$(dd\pi)$	-0.5411	0.1829	-0.7089	0.3193	-0.1910	-1.7396
$(dd\delta)$	0.3357	-0.2430	-1.2726	0.6818	0.4668	2.9257
$(s1s^*2\sigma)$	-0.9709	2.3385	7.1707	0.0642	-0.0772	1.9910
$(s2s^*1\sigma)$	3.3994	-5.0239	0.4364	3.0872	-0.2349	12.4053
$(s^*1p2\sigma)$	-2.7234	-4.8008	1.7586	-2.5451	0.5351	16.9906
$(s^*2p1\sigma)$	4.5299	5.7515	0.6181	0.6516	4.6082	4.5138
$(s^*1d2\sigma)$	2.8069	-1.7050	3.4076	1.0414	-3.8518	12.5601
$(s^*2d1\sigma)$	0.2943	-2.6707	-1.6950	-2.1579	2.2004	-3.5301
$(s^*s^*\sigma)$	3.8433	-3.8555	0.3662	1.4586	0.7470	-5.2658